

2SC5287

Silicon NPN Triple Diffused Planar Transistor (High Voltage Switching Transistor)

Application : Switching Regulator and General Purpose

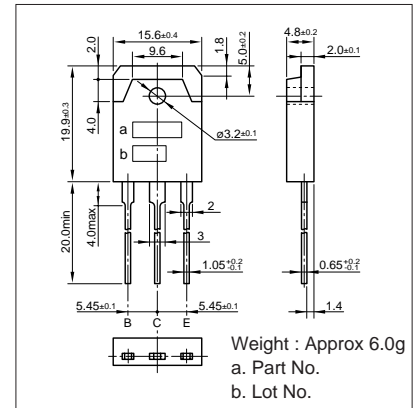
Absolute maximum ratings (Ta=25°C)

Symbol	Rated	Unit
V _{CB0}	900	V
V _{CEO}	550	V
V _{EBO}	7	V
I _C	5(Pulse10)	A
I _B	2.5	A
P _C	80(Tc=25°C)	W
T _j	150	°C
T _{stg}	-55 to +150	°C

Electrical Characteristics (Ta=25°C)

Symbol	Conditions	Rated	Unit
I _{CB0}	V _{CB} =800V	100max	μA
I _{EBO}	V _{EB} =7V	100max	μA
V _{(BR)CEO}	I _C =10mA	550min	V
h _{FE}	V _{CE} =4V, I _C =1.8A	10to25	
V _{CE(sat)}	I _C =1.8A, I _B =0.36A	0.5max	V
V _{BE(sat)}	I _C =1.8A, I _B =0.36A	1.2max	V
f _r	V _{CE} =12V, I _E =-0.35A	6typ	MHZ
COB	V _{CB} =10V, f=1MHZ	50typ	pF

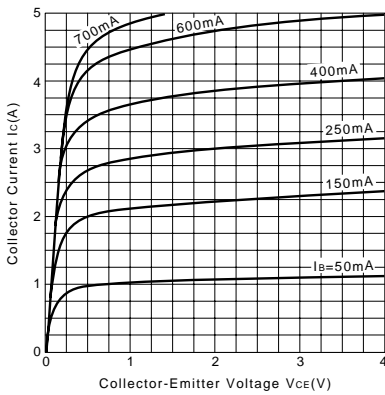
External Dimensions MT-100(TO3P)



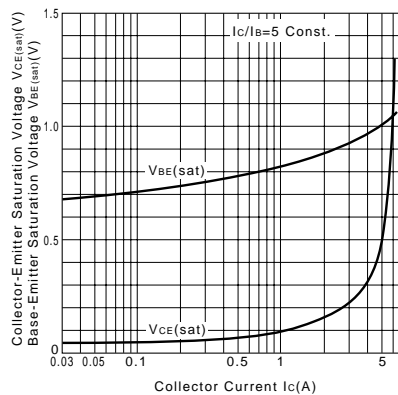
Typical Switching Characteristics (Common Emitter)

V _{CC} (V)	R _L (Ω)	I _C (A)	V _{BB1} (V)	V _{BB2} (V)	I _{B1} (A)	I _{B2} (A)	t _{on} (μs)	t _{stg} (μs)	t _r (μs)
250	139	1.8	10	-5	0.27	-0.9	0.7max	4.0max	0.5max

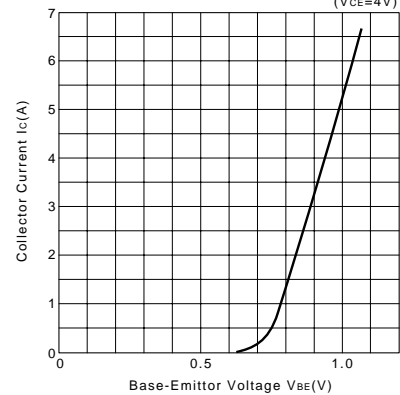
I_C-V_{CE} Characteristics (Typical)



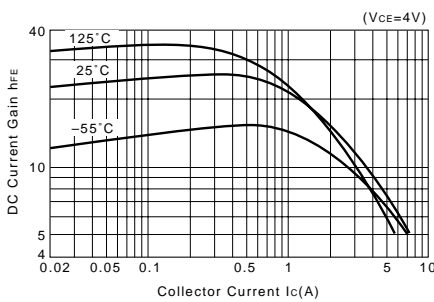
V_{CE(sat)}, V_{BE(sat)}-I_C Temperature Characteristics (Typical)



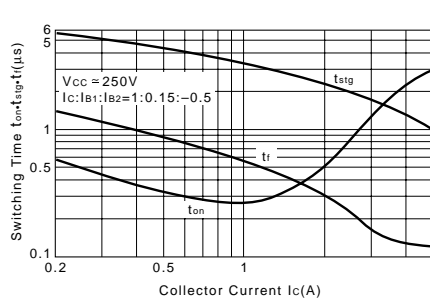
I_C-V_{BE} Temperature Characteristics (Typical)



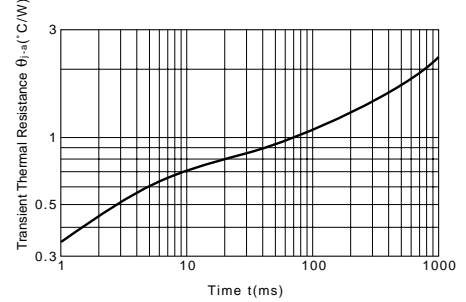
h_{FE}-I_C Characteristics (Typical)



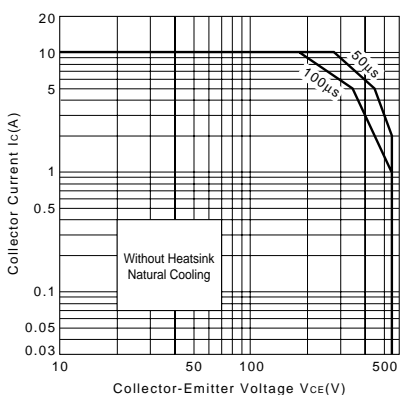
t_{on}*t_{stg}*t_r-I_C Characteristics (Typical)



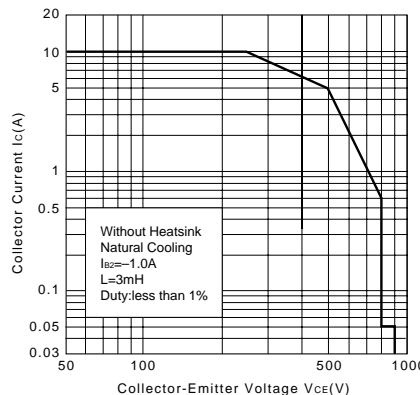
θ_{j-a}-t Characteristics



Safe Operating Area (Single Pulse)



Reverse Bias Safe Operating Area



P_C-T_a Derating

